



PDTB143ETVL Information



For Reference Only

Part Number PDTB143ETVL
Manufacturer Nexperia USA Inc.

Category Discrete Semiconductor Products

Transistors - Bipolar (BJT) - Single, Pre-Biased

Description TRANS PREBIAS PNP 0.46W **Package** TO-236-3, SC-59, SOT-23-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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PDTB143ETVL Specifications

Manufacturer Part NumberPDTB143ETVLManufacturerNexperia USA Inc.CategoryDiscrete Semiconductor ProductsPackageTO-236-3, SC-59, SOT-23-3Series-Transistor TypePNP - Pre-BiasedCurrent - Collector (Ic) (Max)500mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)4.7kResistor - Emitter Base (R2) (Ohms)4.7kDC Current Gain (hFE) (Min) @ Ic, Vce60 @ 50mA, 5VVce Saturation (Max) @ Ib, Ic100mV @ 2.5mA, 50mACurrent - Collector Cutoff (Max)500nAFrequency - Transition140MHzPower - Max320mWMounting TypeSurface MountPackage / CaseTO-236-3, SC-59, SOT-23-3Supplier Device PackageTO-236AB (SOT23)	•	
Category Discrete Semiconductor Products Transistors - Bipolar (BJT) - Single, Pre-Biased Package TO-236-3, SC-59, SOT-23-3 Series - Transistor Type PNP - Pre-Biased Current - Collector (Ic) (Max) Voltage - Collector Emitter Breakdown (Max) Resistor - Base (R1) (Ohms) Resistor - Emitter Base (R2) (Ohms) DC Current Gain (hFE) (Min) @ Ic, Vce 60 @ 50mA, 5V Vce Saturation (Max) @ Ib, Ic 100mV @ 2.5mA, 50mA Current - Collector Cutoff (Max) Frequency - Transition 140MHz Power - Max Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package TO-236AB (SOT23)	Manufacturer Part Number	PDTB143ETVL
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Package TO-236-3, SC-59, SOT-23-3 Series Transistor Type PNP - Pre-Biased Current - Collector (Ic) (Max) Voltage - Collector Emitter Breakdown (Max) Resistor - Base (R1) (Ohms) 4.7k Resistor - Emitter Base (R2) (Ohms) DC Current Gain (hFE) (Min) @ Ic, Vce Vee Saturation (Max) @ Ib, Ic 100mV @ 2.5mA, 50mA Current - Collector Cutoff (Max) Frequency - Transition 140MHz Power - Max Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package TO-236AB (SOT23)	Category	Discrete Semiconductor Products
Series - Transistor Type PNP - Pre-Biased Current - Collector (Ic) (Max) 500mA Voltage - Collector Emitter Breakdown (Max) 50V Resistor - Base (R1) (Ohms) 4.7k Resistor - Emitter Base (R2) (Ohms) 4.7k DC Current Gain (hFE) (Min) @ Ic, Vce 60 @ 50mA, 5V Vce Saturation (Max) @ Ib, Ic 100mV @ 2.5mA, 50mA Current - Collector Cutoff (Max) 500nA Frequency - Transition 140MHz Power - Max 320mW Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package TO-236AB (SOT23)		Transistors - Bipolar (BJT) - Single, Pre-Biased
Transistor Type Current - Collector (Ic) (Max) Voltage - Collector Emitter Breakdown (Max) Resistor - Base (R1) (Ohms) Resistor - Emitter Base (R2) (Ohms) DC Current Gain (hFE) (Min) @ Ic, Vce Vce Saturation (Max) @ Ib, Ic Current - Collector Cutoff (Max) Frequency - Transition Power - Max Mounting Type Surface Mount Package / Case Supplier Device Package PNP - Pre-Biased 500mA 500mA 4.7k 60 @ 50mA, 5V 100mV @ 2.5mA, 50mA 500nA 140MHz 500nA TO-236-3, SC-59, SOT-23-3 Supplier Device Package	Package	TO-236-3, SC-59, SOT-23-3
Current - Collector (Ic) (Max) Voltage - Collector Emitter Breakdown (Max) Resistor - Base (R1) (Ohms) 4.7k Resistor - Emitter Base (R2) (Ohms) DC Current Gain (hFE) (Min) @ Ic, Vce 60 @ 50mA, 5V Vce Saturation (Max) @ Ib, Ic 100mV @ 2.5mA, 50mA Current - Collector Cutoff (Max) Frequency - Transition 140MHz Power - Max 320mW Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package TO-236AB (SOT23)	Series	-
Voltage - Collector Emitter Breakdown (Max) Resistor - Base (R1) (Ohms) 4.7k Resistor - Emitter Base (R2) (Ohms) 4.7k DC Current Gain (hFE) (Min) @ Ic, Vce 60 @ 50mA, 5V Vce Saturation (Max) @ Ib, Ic 100mV @ 2.5mA, 50mA Current - Collector Cutoff (Max) Frequency - Transition 140MHz Power - Max 320mW Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package TO-236AB (SOT23)	Transistor Type	PNP - Pre-Biased
Resistor - Base (R1) (Ohms) Resistor - Emitter Base (R2) (Ohms) DC Current Gain (hFE) (Min) @ Ic, Vce 60 @ 50mA, 5V Vce Saturation (Max) @ Ib, Ic 100mV @ 2.5mA, 50mA Current - Collector Cutoff (Max) Frequency - Transition 140MHz Power - Max 320mW Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package TO-236AB (SOT23)	Current - Collector (Ic) (Max)	500mA
Resistor - Emitter Base (R2) (Ohms) DC Current Gain (hFE) (Min) @ Ic, Vce 60 @ 50mA, 5V Vce Saturation (Max) @ Ib, Ic 100mV @ 2.5mA, 50mA Current - Collector Cutoff (Max) Frequency - Transition 140MHz Power - Max 320mW Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package TO-236AB (SOT23)	Voltage - Collector Emitter Breakdown (Max)	50V
DC Current Gain (hFE) (Min) @ Ic, Vce 60 @ 50mA, 5V Vce Saturation (Max) @ Ib, Ic 100mV @ 2.5mA, 50mA Current - Collector Cutoff (Max) 500nA Frequency - Transition 140MHz Power - Max 320mW Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package TO-236AB (SOT23)	Resistor - Base (R1) (Ohms)	4.7k
Vce Saturation (Max) @ Ib, Ic100mV @ 2.5mA, 50mACurrent - Collector Cutoff (Max)500nAFrequency - Transition140MHzPower - Max320mWMounting TypeSurface MountPackage / CaseTO-236-3, SC-59, SOT-23-3Supplier Device PackageTO-236AB (SOT23)	Resistor - Emitter Base (R2) (Ohms)	4.7k
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Frequency - Transition 140MHz Power - Max 320mW Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package TO-236AB (SOT23)	Vce Saturation (Max) @ Ib, Ic	100mV @ 2.5mA, 50mA
Power - Max 320mW Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package TO-236AB (SOT23)	Current - Collector Cutoff (Max)	500nA
Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package TO-236AB (SOT23)	Frequency - Transition	140MHz
Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package TO-236AB (SOT23)	Power - Max	320mW
Supplier Device Package TO-236AB (SOT23)	Mounting Type	Surface Mount
•	Package / Case	TO-236-3, SC-59, SOT-23-3
Report errors?	Supplier Device Package	TO-236AB (SOT23)
		Report errors?

PDTB143ETVL Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

PDTB143ETVL Payment Methods



















PDTB143ETVL Shipping Methods













If you have any question about PDTB143ETVL, please do not hesitate to contact us!

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